



InP membrane technology platform for large scale photonic integration

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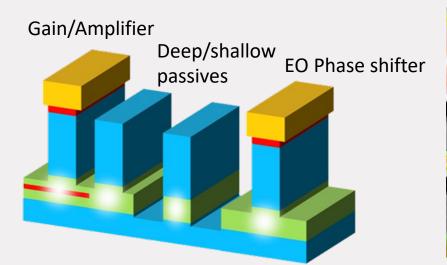


Outline

- Introduction
- Laser integrated nanophotonics platform
- Key components for large scale and high capacity
- Summary

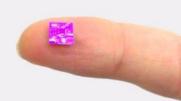


Photonic integration on InP







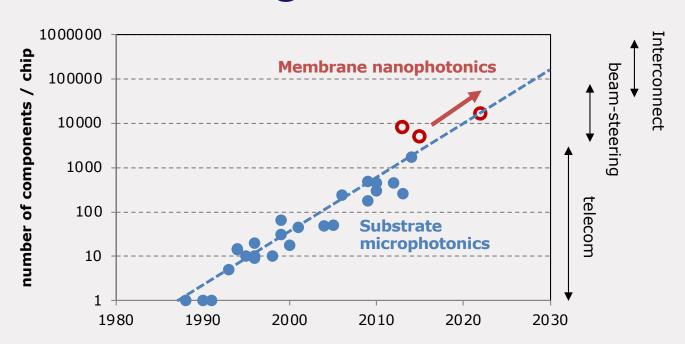


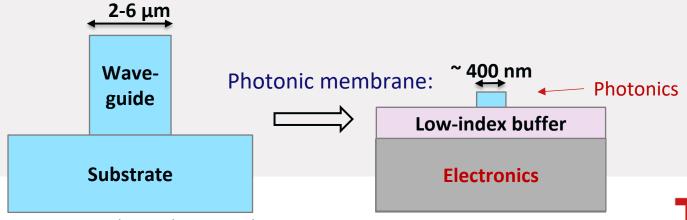


From micro to nano integration

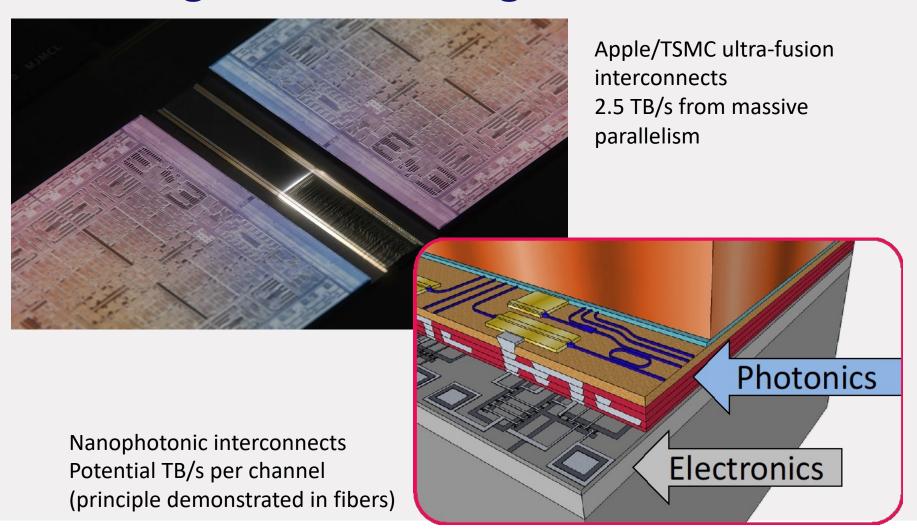
Driving force:

- Functionality
- Speed
- Energy efficiency



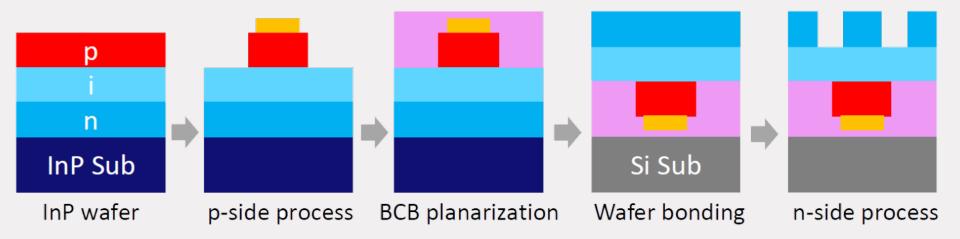


Heterogeneous co-integration

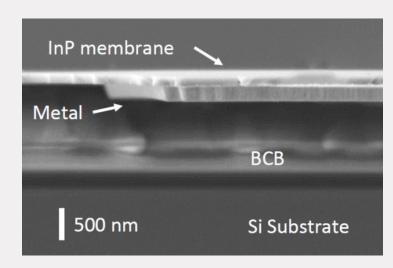




Double-sided InP membrane



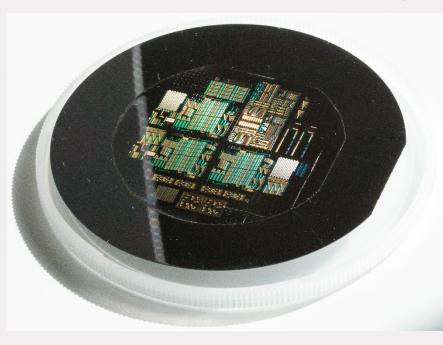
- x2 times ultra-flat surfaces for highest lithography precision
- enable deep UV 193nm scanner process (CD 100 nm)
- design freedom for optimal optical and electrical performances

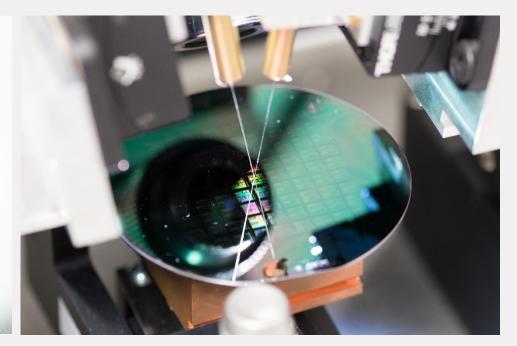




Wafer-scale integration for membrane

Wafer-to-wafer bonding



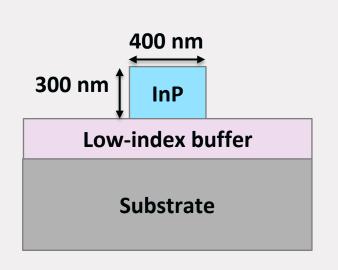


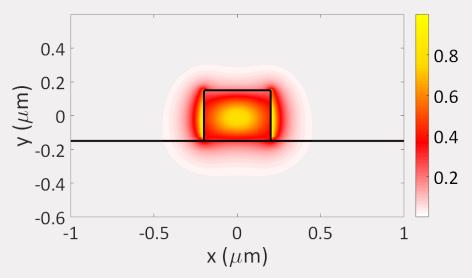
- 2-inch wafer scale
- A/P membrane 1.5 μm thick
- Patterned with EBL

- Full 3-inch wafer scale
- Membrane only 300 nm thick
- Patterned with ASML DUV scanner
- Route to sub-dB/cm loss

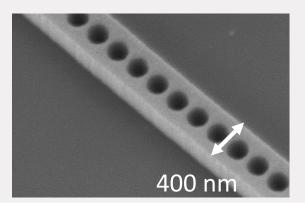


High optical confinement in InP

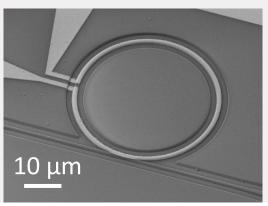




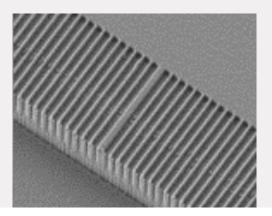
Enabling high-performance laser cavities:



R > 98% PhC mirrors ($L = 3 \mu m$)



Q > 60,000 resonators

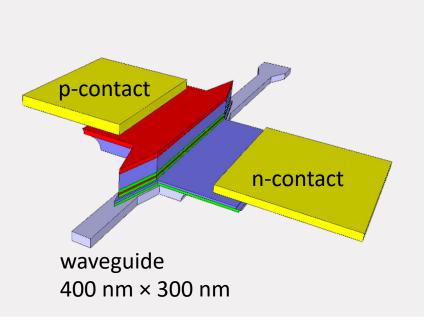


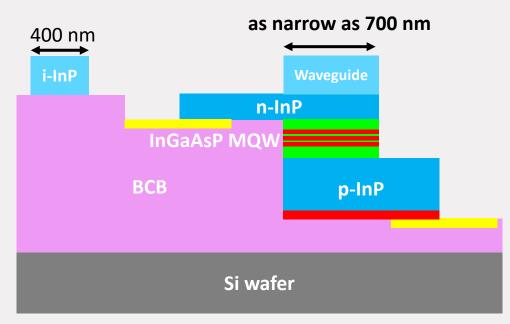
Distributed feedback mirrors



Native gain in nanophotonic waveguides

- S-shaped amplifier/laser for tighter confinement
- Improve optical mode matching
- No critical alignment (lithography overlay accuracy)

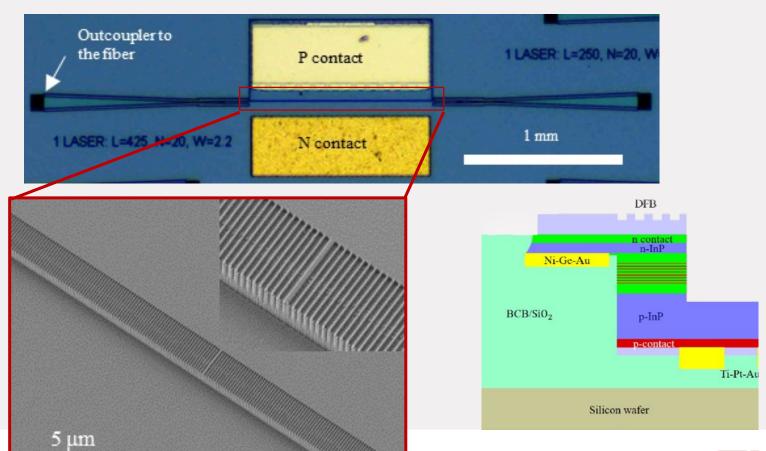






DFB lasers

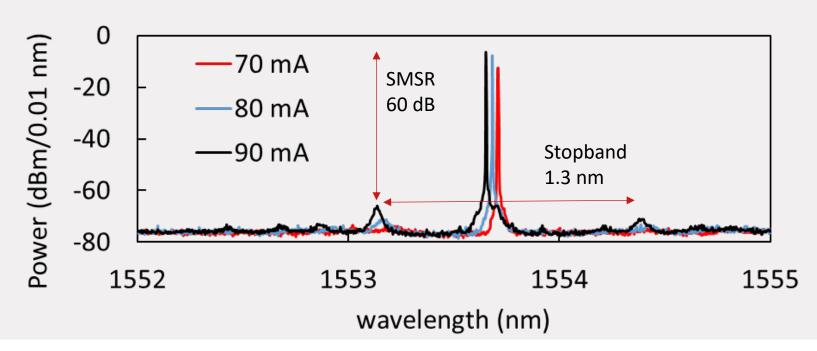
• Quarter- λ shifted DFB cavity (1 mm long)





DFB lasers

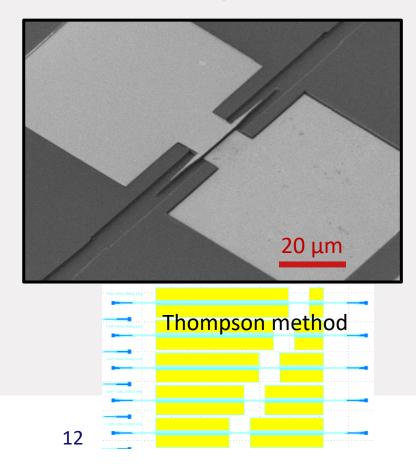
- 50mA threshold current (2.5 kA/cm²)
- 1 mW in fiber (10 mW in waveguide)
- Very high SMSR > 60dB

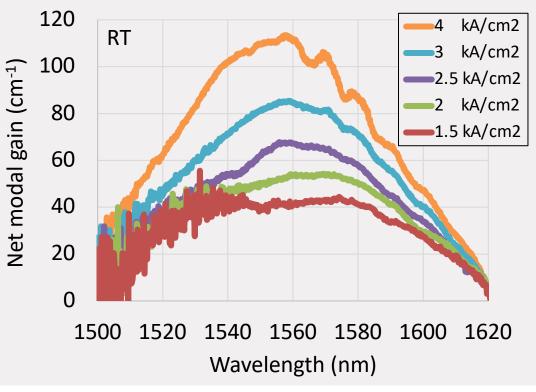




Membrane amplifier

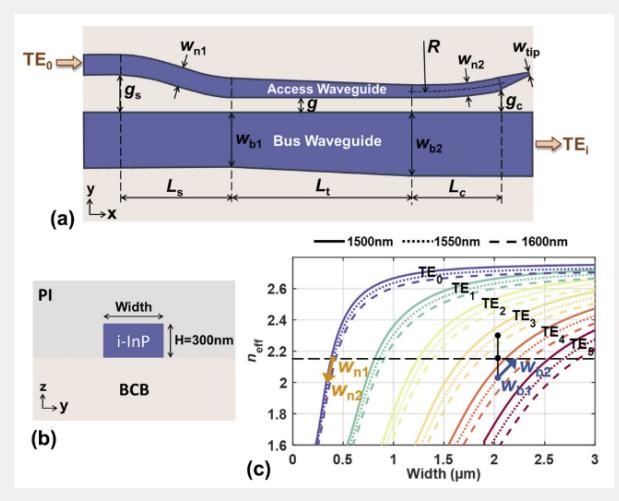
- 4 / 8 multi-quantum wells (MWQ) design
- 110 cm⁻¹ gain @ 4 kA cm⁻² (8 MQW)







Multimode multiplexing



5-mode multiplxer on InP

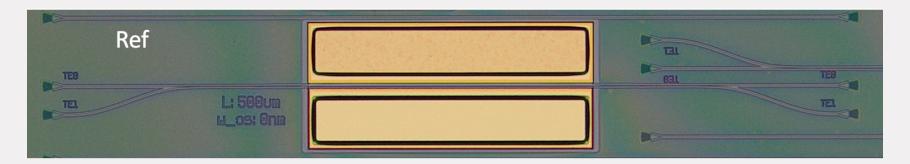
EL < 1 dB, XT < -14 dB with 50nm width variation

Broadband (~ 100nm)

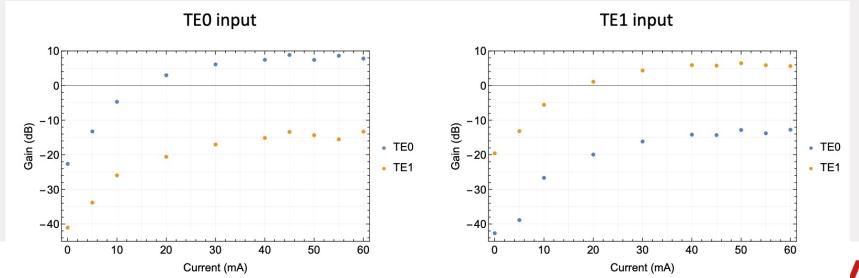
Highest tolerance reported thanks to moderate index contrast



Multimodal amplification



Preliminary results of a test amplifier (500um) for TE0 and TE1 8 dB gain for TE0, 6 dB for TE1 @ 50mA injection

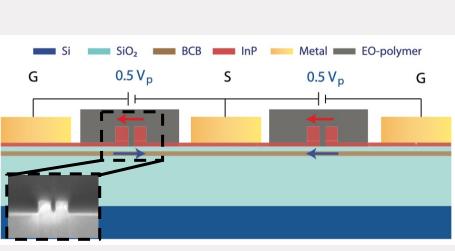


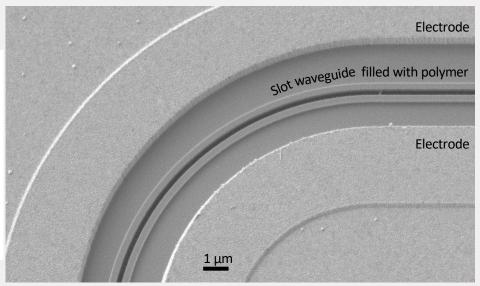


First EO polymer modulator on InP

InP has 3x lower optical loss and 8x higher electron mobility than Si, at same doping level (1e18 cm⁻³)

First electro-optic polymer modulator on InP





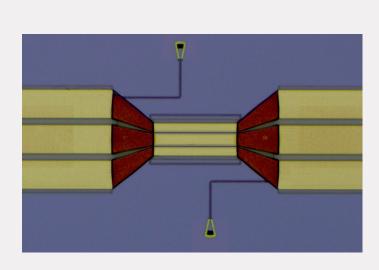


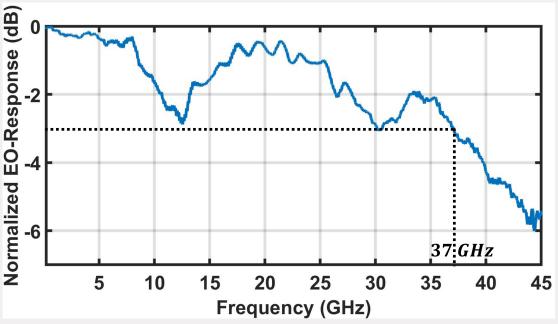
First EO polymer modulator on InP

Conservative material choice: bulk r33 coefficient 110 pm/V,

Effective r33 in slot 25 pm/V due to surface effects

37GHz bandwidth & 4.5 V.mm achieved

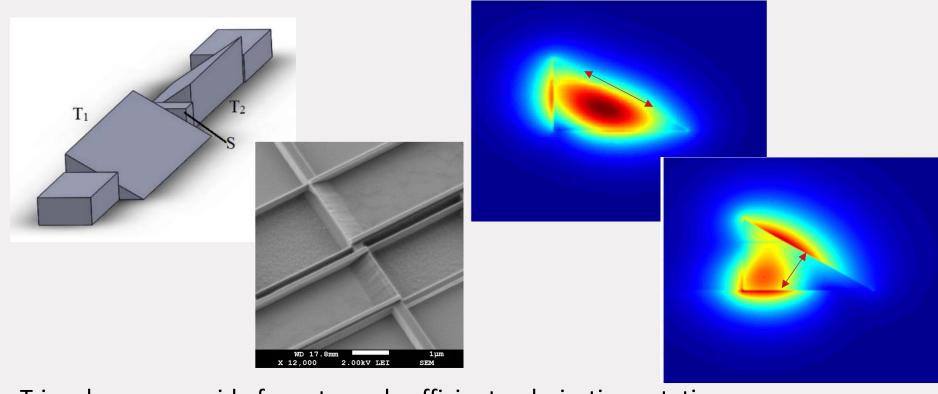






IEEE JQE, vol. 57, pp. 1-10, 2021. Manuscirpt in preparation

On-chip polarization handling



Triangluar waveguide for extremely efficient polarization rotation High fab tolerances by exploiting natural "slow-etch" crystal plane Full TE/TM conversion (> 99%) within $4.2~\mu m$ length (record small)



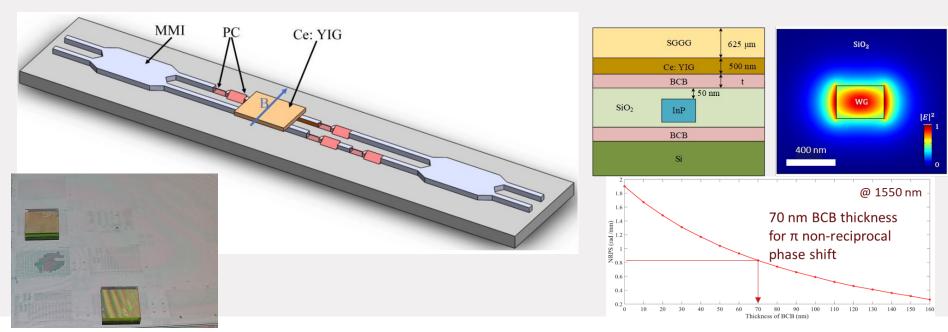
Integrated isolator/circulator

First on-chip isolator on InP PICs (37 dB isolation demonstrated)

Direct integration <u>right next to</u> the InP lasers

Novel polarization insensitive design

First technological success in 3D integration (YIG + InP + Si)

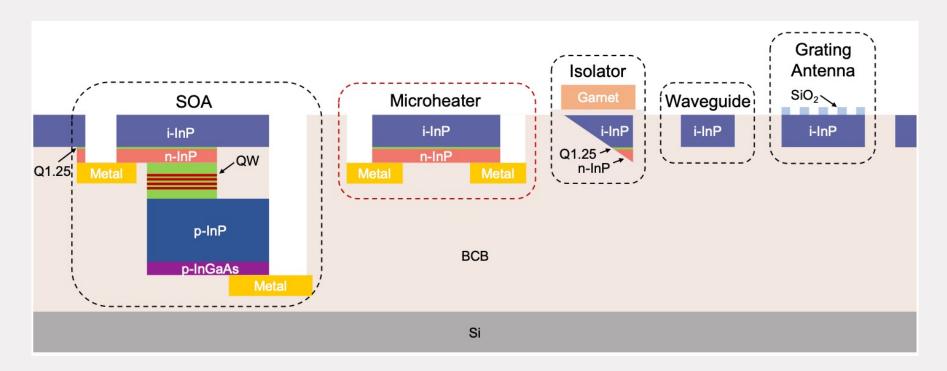




Provisional EU Patent No. 2028831 Optica vol. 8, pp. 1654-1661, 2021.

The platform

- One-stop shop to access amplifier/laser, (slot) waveguides, polarization controllers, microheaters, resonators and more.
- Officially a JePPIX product. Please visit JePPIX booth at ECOC2022





Summary

- Active-passive photonic integration on an InP membrane
- InP membrane enables fab-tolerant components, efficient gain and flexible material integration
- A viable technology towards very-large-scale integration









